

FORM PTO-1449

U.S. Department of Commerce  
Patent and Trademark OfficeAttorney Docket Number  
5308-157IP2Serial No.  
10/045,542

## LIST OF DOCUMENTS CITED BY APPLICANT

(Use several sheets if necessary)

Applicants: Das et al.

Filing Date: October 26, 2001

Group: 1762

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Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
7	1	3,924,024	12/2/75	Naber et al.	427	95	
	2	4,466,172	8/21/84	Batra	29	571	
	3	4,875,083	10/17/89	Palmour	357	23.6	
	4	5,170,455	12/8/92	Goossen et al.	385	89	
	5	5,184,199	2/2/93	Fujii et al.	29	10	
	6	5,506,421	4/9/96	Palmour	257	77	
	7	5,510,630	4/23/96	Agarwal et al.	257	77	
	8	5,726,463	3/10/98	Brown et al.	257	77	
	9	5,763,905	6/9/98	Harris	257	77	
	10	5,837,572	11/17/98	Gardner et al.	438	199	
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7	24	WO 97/17730	5/15/97	PCT	—	—	

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7	25	WO 97/39485	10/23/97	PCT			
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✓	7	26	M. K. Das, L.A. Lipkin, J.W. Palmour, G.Y. Chung, J.R. Williams, K. McDonald, and L.C. Feldman, "High Mobility 4H-SiC Inversion Mode MOSFETs Using Thermally Grown, NO Annealed SiO <sub>2</sub> ," <i>IEEE Device Research Conference</i> , Denver, CO June 19-21, 2000.				
✓		27	G.Y. Chung, C.C. Tin, J.R. Williams, K. McDonald, R.A. Weller, S.T. Pantelides, L.C. Feldman, M.K. Das, and J.W. Palmour, "Improved Inversion Channel Mobility for 4H-SiC MOSFETs Following High Temperature Anneals in Nitric Oxide," <i>IEEE Electron Device Letters</i> accepted for publication.				
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17	1	6,054,352	4/25/00	Ueno	438	268	
<b>FOREIGN PATENT DOCUMENTS</b>							
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<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							

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